

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

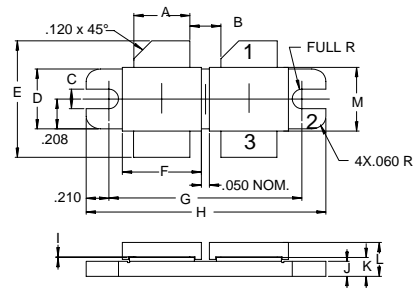
The **ASI AVF1000** is a common base transistor Designed for pulsed systems Applications up to 1090 MHz.

FEATURES:

- Internal Input/Output Matching Networks
- $P_G = 6.0$ dB at 1000W/1090 MHz
- **OmnigoldTM** Metalization System

MAXIMUM RATINGS

I_C	65 A
V_{CES}	55 V
V_{EBO}	3.5 V
P_{DISS}	2900 W @ T_C 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.06 °C/W

PACKAGE STYLE .450 BAL FLG (B)


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.373 / 9.47	.385 / 9.78
B	.205 / 5.21	
C	.120 / 3.25	.130 / 3.30
D	.411 / 10.44	.421 / 10.69
E	.825 / 20.96	.865 / 21.97
F	.525 / 13.34	.535 / 13.59
G	1.255 / 31.88	1.265 / 32.18
H	1.675 / 42.55	1.685 / 42.80
I	.002 / 0.05	.006 / 0.15
J	.095 / 2.41	.105 / 2.67
K	.115 / 2.92	.135 / 3.43
L	.250 / 6.35	
M	.445 / 11.30	.457 / 11.61

1 = Collector 2 = Base 3 = Emitter

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 100$ mA	65			V
BV_{EBO}	$I_E = 50$ mA	3.5			V
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10			---
P_{OUT}	F = 1090 MHz	1000			W
P_{IN}	$V_{CC} = 45$ V			250	W
P_G	PW = 10 μ sec	6.0			dB
η_C	DF = 1 %		43		%
t_r				70	ns
$VSRW^1$	F = 1030 MHz			9:1	

Note 1: At rated output power and pulse conditions.